

# GD50MPS12-CAL

## 1200V 50A SiC Schottky MPS™ Diode



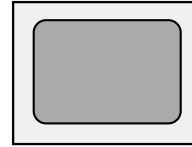
### Silicon Carbide Schottky Diode

V <sub>RRM</sub>	=	1200 V
I <sub>F</sub> (T <sub>C</sub> = 147°C)	=	50 A
Q <sub>C</sub>	=	161 nC

#### Features

- Gen4 Thin Chip Technology for Low V<sub>F</sub>
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Q<sub>C</sub>/I<sub>F</sub>
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V<sub>F</sub>
- High dV/dt Ruggedness

#### Bare Chip



#### Advantages

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

#### Applications

- Electric Vehicles and Fast Chargers
- Solar Inverters
- Train Auxiliary Power Supplies
- High frequency Converters
- Motor Drives
- Induction Heating and Welding
- Uninterruptible Power Supplies
- Pulsed Power

#### Absolute Maximum Ratings (At T<sub>C</sub> = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>		1200	V	
Continuous Forward Current	I <sub>F</sub>	T <sub>C</sub> = 100°C, D = 1	92	A	Fig. 4
		T <sub>C</sub> = 135°C, D = 1	63		
		T <sub>C</sub> = 147°C, D = 1	50		
Non-Repetitive Peak Forward Surge Current, Half Sine Wave	I <sub>F,SM</sub>	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10 ms	500	A	
		T <sub>C</sub> = 150°C, t <sub>p</sub> = 10 ms	400		
Repetitive Peak Forward Surge Current, Half Sine Wave	I <sub>F,RM</sub>	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10 ms	300	A	
		T <sub>C</sub> = 150°C, t <sub>p</sub> = 10 ms	210		
Non-Repetitive Peak Forward Surge Current	I <sub>F,MAX</sub>	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10 μs	2500	A	
i <sup>2</sup> t Value	∫i <sup>2</sup> dt	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10 ms	1250	A <sup>2</sup> s	
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	L = 0.4 mH, I <sub>AS</sub> = 50 A	541	mJ	
Diode Ruggedness	dV/dt	V <sub>R</sub> = 0 ~ 960 V	200	V/ns	
Power Dissipation	P <sub>TOT</sub>	T <sub>C</sub> = 25°C	519	W	Fig. 3
Operating and Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>		-55 to 175	°C	

\*Assumes Thermal Resistance, Junction - Case (R<sub>thJC</sub>) of 0.29°C/W

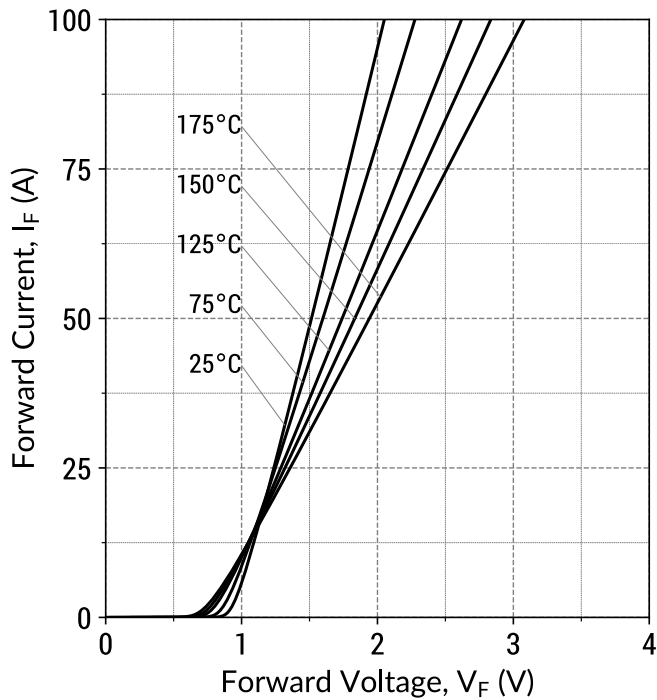
### Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Diode Forward Voltage	$V_F$	$I_F = 50 \text{ A}, T_j = 25^\circ\text{C}$		1.5	1.8	V	Fig. 1
		$I_F = 50 \text{ A}, T_j = 175^\circ\text{C}$		1.9			
Reverse Current	$I_R$	$V_R = 1200 \text{ V}, T_j = 25^\circ\text{C}$		3	15	$\mu\text{A}$	Fig. 2
		$V_R = 1200 \text{ V}, T_j = 175^\circ\text{C}$		33			
Total Capacitive Charge	$Q_C$	$I_F \leq I_{F,MAX}$ $di_F/dt = 200 \text{ A}/\mu\text{s}$	$V_R = 400 \text{ V}$	111		nC	Fig. 7
			$V_R = 800 \text{ V}$	161			
Switching Time	$t_s$	$di_F/dt = 200 \text{ A}/\mu\text{s}$	$V_R = 400 \text{ V}$	< 10		ns	
			$V_R = 800 \text{ V}$				
Total Capacitance	C	$V_R = 1 \text{ V}, f = 1\text{MHz}$		1835		pF	Fig. 6
		$V_R = 800 \text{ V}, f = 1\text{MHz}$		107			

### Mechanical Parameters

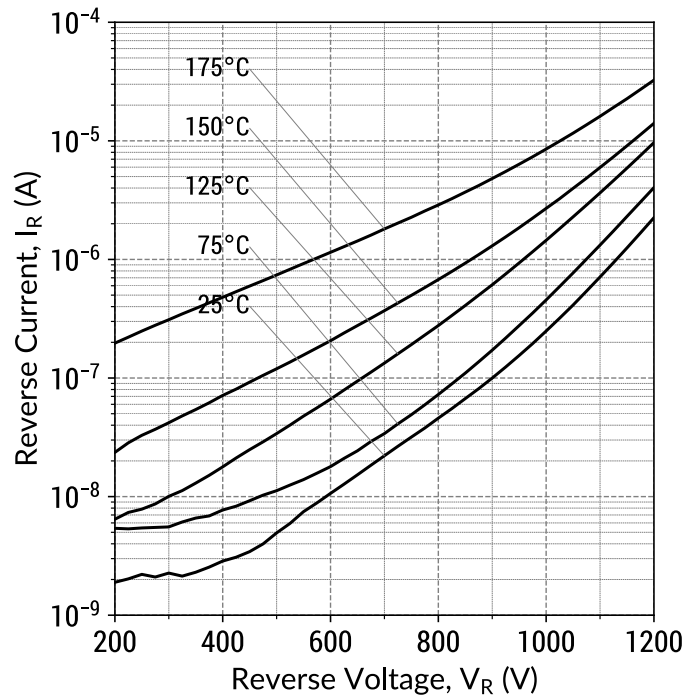
This information is **confidential**, please contact [sales@genesicsemi.com](mailto:sales@genesicsemi.com) to learn more.

Figure 1: Typical Forward Characteristics



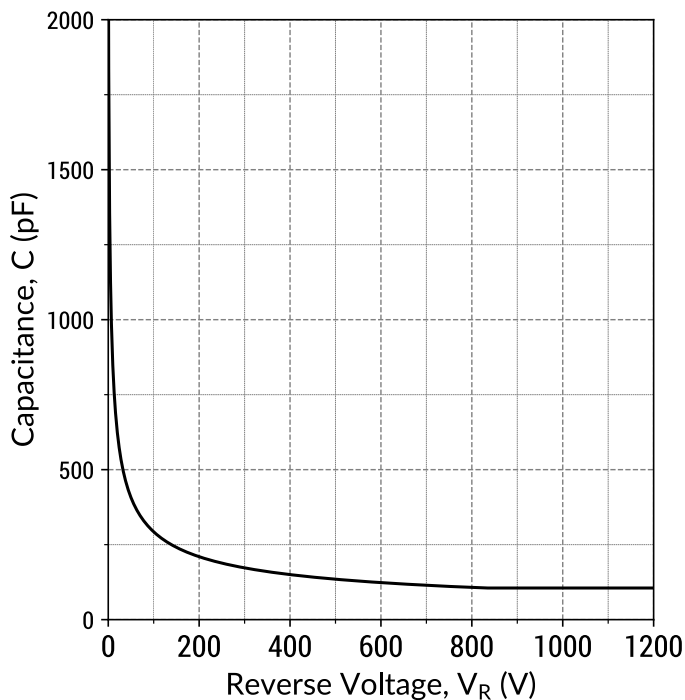
$$I_F = f(V_F, T_j); t_P = 250 \mu s$$

Figure 2: Typical Reverse Characteristics



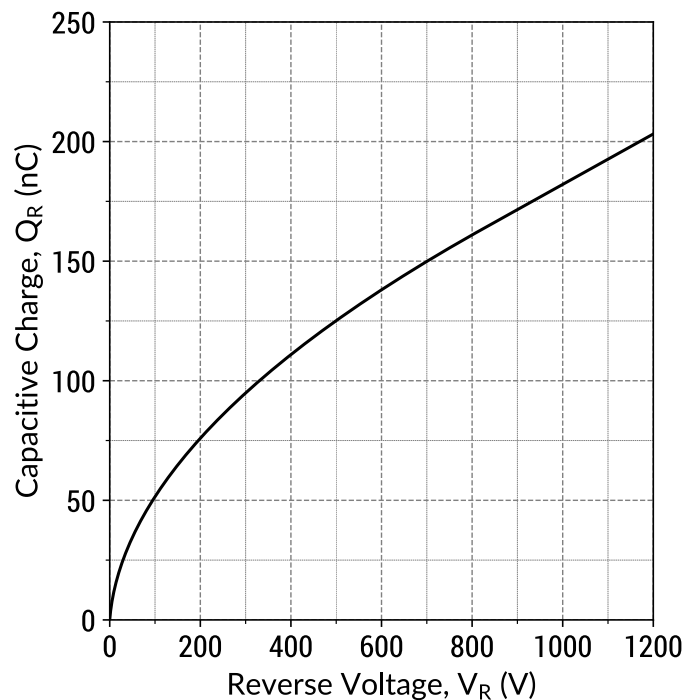
$$I_R = f(V_R, T_j)$$

Figure 3: Typical Junction Capacitance vs Reverse Voltage Characteristics



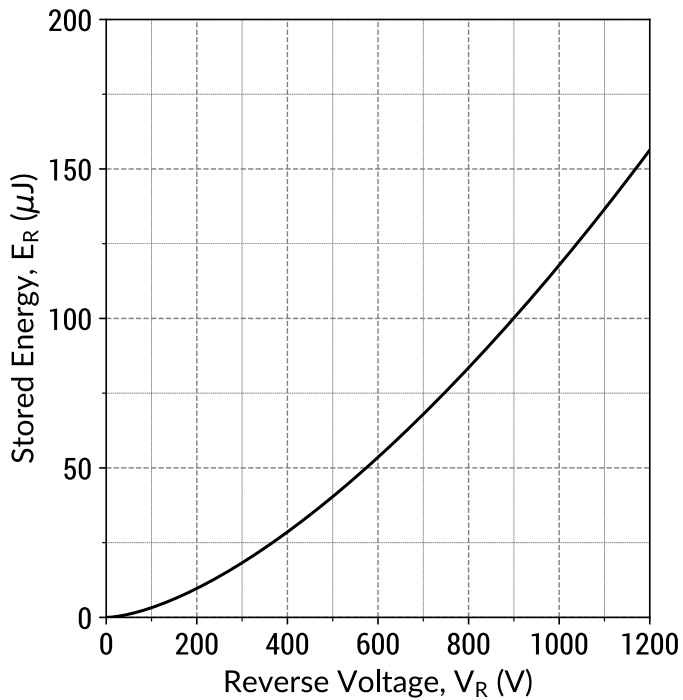
$$C = f(V_R); f = 1 \text{ MHz}$$

Figure 4: Typical Capacitive Charge vs Reverse Voltage Characteristics



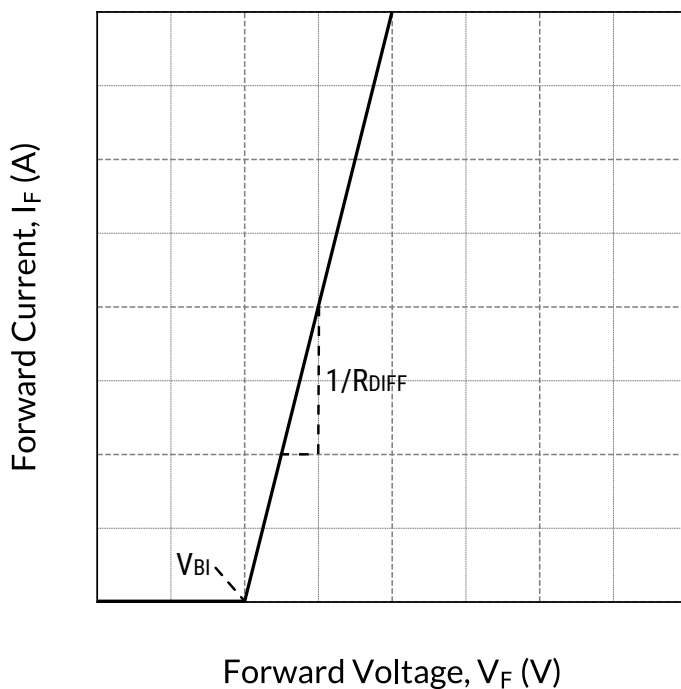
$$Q_C = f(V_R); f = 1 \text{ MHz}$$

Figure 5: Typical Capacitive Energy vs Reverse Voltage Characteristics



$$E_C = f(V_R); f = 1\text{MHz}$$

Figure 6: Forward Curve Model



$$I_F = f(V_F, T_j)$$

**Forward Curve Model Equation:**

$$I_F = (V_F - V_{BI})/R_{DIFF} \text{ (A)}$$

**Built-In Voltage (V<sub>BI</sub>):**

$$V_{BI}(T_j) = m \times T_j + n \text{ (V)}$$

$$m = -0.00119 \text{ (V/°C)}$$

$$n = 1.01 \text{ (V)}$$

**Differential Resistance (R<sub>DIFF</sub>):**

$$R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c \text{ (}\Omega\text{)}$$

$$a = 2.38e-07 \text{ (}\Omega\text{/°C}^2\text{)}$$

$$b = 3.3e-05 \text{ (}\Omega\text{/°C)}$$

$$c = 0.00979 \text{ (}\Omega\text{)}$$

**Forward Power Loss Equation:**

$$P_{LOSS} = V_{BI}(T_j) \times I_{AVG} + R_{DIFF}(T_j) \times I_{RMS}^2$$

### Chip Dimensions

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#### NOTE

1. CONTROLLED DIMENSION IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.

## Compliance

### RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

### REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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## Related Links

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## Revision History

Date	Revision	Comments	Supersedes
07/09/2020	Rev 1	Initial Release	



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